

MSKSEMI 美森科

SEMICONDUCTOR



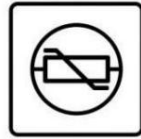
ESD



TVS



TSS



MOV



GDT



PLED

LM321

Product Brochure

Product Introduction

LM321 is a single-output low-power differential operational amplifier that can be powered by a single or dual power supply. It has high open-loop gain, internal compensation, high common

The module has a wide range of analog and temperature stability, as well as output short-circuit protection. It can be applied to sensor amplifier circuits, DC amplifier modules, audio amplifier circuits and

In traditional operational amplifier circuits

Features

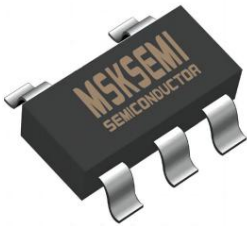
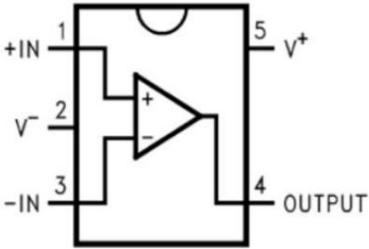

- Single power supply voltage range: 3V~36V
- Dual power supply voltage range: ±18V
- Unity gain bandwidth: up to 1.2MHZ
- Output short circuit protection
- Low power consumption: 0.5mA @ V+=5V
- Package: SOT-23-5

Product Usage

- Sensor signal amplifier
- DC gain
- Audio amplifier
- Other application areas

Package and pinout

Define functionality

Package	Pin Definition	Silkscreen
 TODAY-23-5		

SOT23-5 pin number and pin definition		Functional Description
1	IN+	Non-inverting input
2	V-	Negative power supply
3	IN-	Inverting input
4	OUTPUT	Output
5	V+	Power positive

Limit parameters

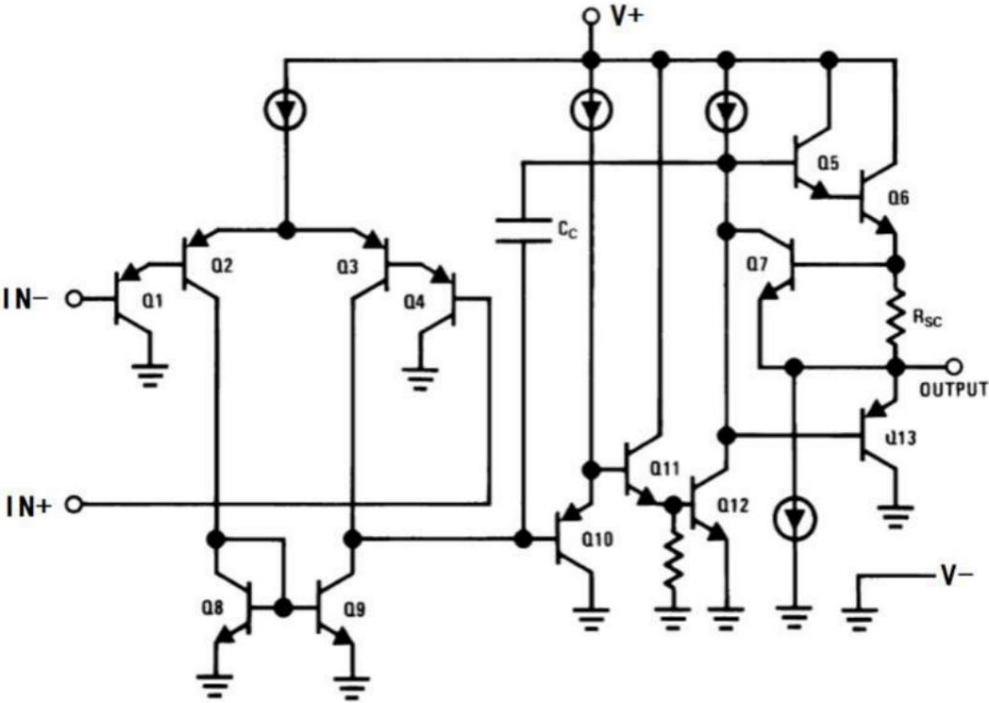
Project	symbol	Limit value (1)	unit
Single power supply voltage	V+	40	In
Dual power supply voltage	Vs	±20	In
Differential input voltage (2)	WIND	±40	In
Common-mode input voltage	VICR	-0.3~40V	In
Output short circuit time	tsc	continuous	
Power dissipation	PD	300	mW
Operating temperature	TJMAX	0-70	°C
Storage temperature	TS	-65-150	°C
Soldering temperature	TW	260,10s	°C

Note: (1) The limit value refers to the limit value that cannot be exceeded under any conditions. If this limit value is reached, it may cause physical damage such as product degradation; at the same time,

When the parameters are close to the limit, the chip cannot be guaranteed to work properly.

(2) The voltage difference between input IN+ and IN-.

Equivalent schematic diagram

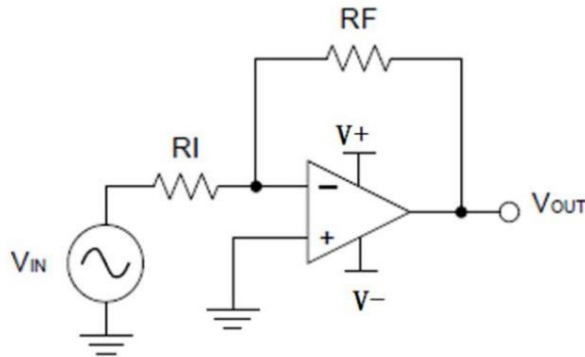


DC Electrical Characteristics (TA=25°C, V+ =5V, V- =GND unless otherwise specified)

project	symbol	Test conditions		Min	Typ	Max	Unit
Input offset voltage	SAW	V+ =5V to MAX, VIC=VICR (min), VO=1.4V				5	mV
Input offset current	IIO	VO = 1.4 V				10	nA
Bias current	IBIAS	VO = 1.4 V				50	nA
Common-mode input voltage	VICR	V+=5V to 36V		V-		V+ -1.5V	In
Open loop voltage gain	AOL	V+=15V,VO=1V to 11V,RL=2kΩ				100	V/mV
Common Mode Rejection Ratio	CMRR	V+=5V to MAX,VIC=VICR (min)		—		80	dB
Unity gain bandwidth	GBWP			—		1.2	MHZ
Power Supply Voltage Rejection Ratio	PSSR	ΔVDD/ΔVIO V+=5V to MAX, f=20kHz				90	dB
Output high level voltage	VOH	V+ =15V, VID=1V	Iout =-50uA			13.6	In
			Iout =-1mA	—		13.5	In
			Iout =-5mA	—		13.4	In
		V+ =28V	RL=2k			26	In
Output low level voltage	VOL	V+ =15V, VID=-1V	Iout =50uA			0.1	In
			Iout =1mA			0.7	In
			Iout =5mA	—		1.0	In
		V+ =28V	RL=2k	—		0.85	In
Power supply operating current	ICC	V+ =5V,VO=1/2V+, No load				0.5	m.a.
		V+ =36,VO=1/2V+, No load				0.8	m.a.
Single power supply operating voltage	V+	V- =0V(GND)		3		36	In
Dual power supply operating voltage	VS	V+,V-		-18		+18	In

Typical Applications

1. Circuit diagram



2. Design requirements

The power supply voltage must be selected to be larger than the input voltage range

and the output range. For example, if the signal source V_{IN} is amplified from $\pm 0.5V$ to $\pm 1.8V$, setting the power supply to $\pm 5V$ is sufficient for this application.

3. Design process

Calculate the amplification factor (gain) according to

$$A_{VF} = -V_O/V_{IN} \quad \text{formula (1): } A_V = \dots\dots\dots(1)$$

$$A_V = -V_O/V_{IN} = -1.8/0.5 = -3.6$$

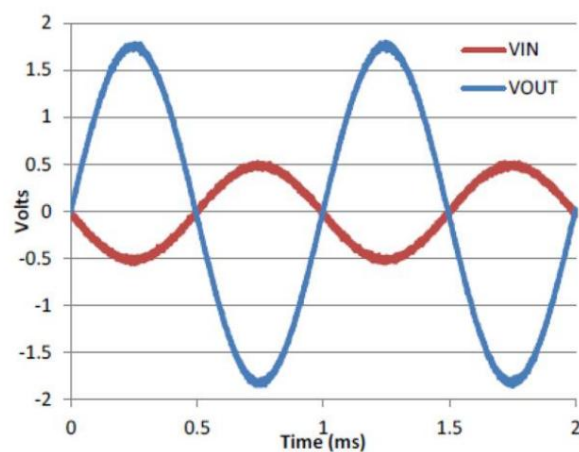
Once the desired gain A_V is determined, a value for the R_I or R_F resistor is selected.

You can choose a value between $1k\Omega$ and $100k\Omega$. In this example, we will choose $R_I = 10k\Omega$, which results in $R_F = 36k\Omega$. This is determined by Equation 2.

$$A_V = -R_F/R_I \quad \dots\dots\dots(2)$$

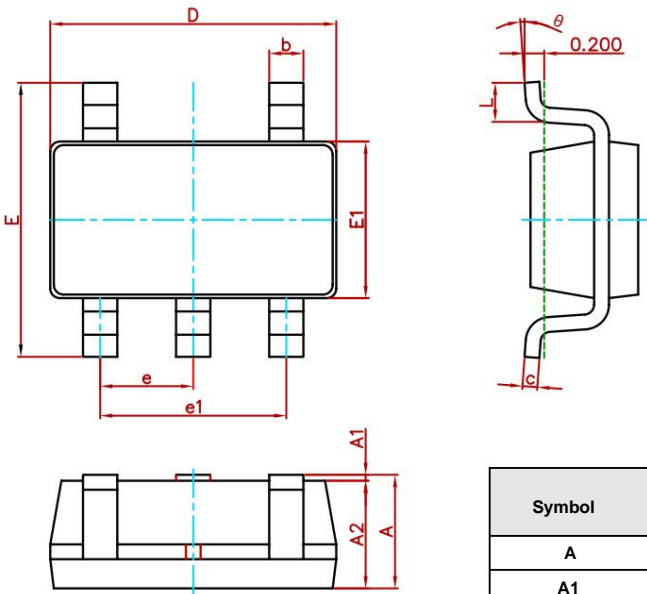
$$R_F = -A_V \cdot R_I = 3.6 \cdot 10 = 36k\Omega$$

4. Application curve chart



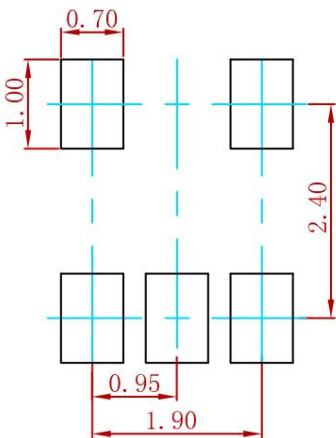
Inverting amplifier input voltage vs output voltage

Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
AND	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
and	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
i	0°	8°	0°	8°

Pad layout



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

Ordering Information

P/N	PKG	QTY
LM321	TODAY-23-5	3000

Attention

Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein. Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law. No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties. Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.